

# ATTL7542 Tip Ring Access Switch

#### **Features**

- Small size/surface-mount packaging
- Monolithic IC reliability
- Clean, bounce-free switching
- Low, matched ON-resistance
- Built-in current limiting, thermal shutdown, and SLIC protection
- Very low power consumption
- No EMI

### **Applications**

- Central office
- DLC
- PBX

# Description

The ATTL7542 Tip Ring Access Switch (TRAS) is a monolithic integrated circuit that contains six solid-state relay contacts designed to replace electromechanical relays (EMR) in central office and digital loop carrier analog line-card applications. Through application of appropriate control signals to two logic level inputs, the idle or talk state, power ring and line test access states are achievable via the TRAS IC. With the addition of a single 2 Form C EMR and associated controls (Figure 9), the ringing-generator test access states and battery-feed test access are realized.

The line break switch pair is a linear switch that has exceptionally low ON-resistance and an excellent ON-resistance matching characteristic. The ringing access switch has a breakdown voltage rating >450 V, which is sufficiently high enough to prevent breakdown (i.e., passing the transient on to the ringing generator) in the presence of a transient fault condition.

Incorporated into the TRAS is a foldover type SLIC protection circuit that limits the voltage seen by the battery feed and shunts currents to a ground device during a fault condition. Thus, the TRAS eliminates the need for a separate SLIC protection device.

To protect the TRAS from an overvoltage fault condition, use of a secondary protector is required. The secondary protector must limit the voltage applied to the TRAS to <250 V. Use of a foldback or crowbar type secondary protector is recommended. The line break switch pair and access switches (except those connected to the ringing generator) have a current-limit feature that will limit the current through the switch in the presence of a transient fault condition.

Also incorporated into the TRAS is a thermal shutdown circuit that will cause the chip to shutdown (all switches off) when excessive power dissipation, such as what is encountered in the presence of an extended power cross, causes the chip temperature to rise above a given threshold. With the proper design of SLIC circuitry, proper selection of secondary protector, and series resistors, the TRAS will meet appropriate regulatory agency requirements.

The TRAS requires 5 V, battery voltage, and ground to operate. The TRAS device is packaged in a 16-pin, plastic SOG package (ATTL7542AAE/BAE).

### Pin Information

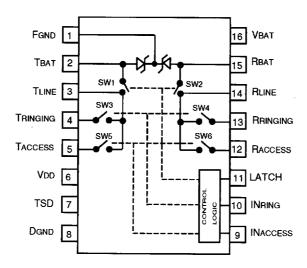


Figure 1. 16-Pin, Plastic SOG

Table 1. Pin Descriptions

Pin	Symbol	Description	Pin	Symbol	Description
1	FGnd	Fault ground.	16	VBAT	Battery voltage.
2	Тват	Connect to TIP on SLIC side.	15	RBAT	Connect to RING on SLIC side.
3	TLINE	Connect to TIP on line side.	14	RLINE	Connect to RING on line side.
4	TRINGING	Connect to return ground for ringing generator.	13	RRINGING	Connect to ringing generator.
5	TACCESS	Test access.	12	RACCESS	Test access.
6	VDD	+5 V supply.	11	LATCH	Data input control, active-high, transparent low.
7	TSD	Temperature shutdown output flag will read +5 V when the device is in its operational mode and 0 V in the thermal shutdown mode. To disable the thermal shutdown mechanism, tie this pin to +5 V.	10	INRINGING	Logic level switch input control
8	DGnd	Digital ground.	9	INACCESS	Logic level switch input control.

### **Electrical Characteristics**

Ta --40 °C to +85 °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information purposes only and are not part of the testing requirements.

**Table 2. Power Supply Specifications** 

Parameter	Power Supply, VDD	Power Supply, VBAT
Nominal Voltage	+5 V	-48 V/-60 V*
Voltage Tolerance	±0.5 V	±20%

<sup>\*</sup> Choice of SLIC protection circuit trigger voltage is determined by the maximum voltage of VBAT. See SLIC Protection Circuit section for details.

Table 3. Break Switch, 1and 2

Parameter	Test Condition	Measure	Min	Тур	Max	Unit
Off-state Leakage Current	Vswitch (differential) = -320 V to Gnd Vswitch (differential) = -60 V to +260 V	Iswitch	_	_	1	μA
ON Resistance	Iswitch (on) = $\pm 10$ mA, $\pm 40$ mA	Δ Von		15 *	28	Ω
ON-resistance Match	Per ON-resistance Test Condition of SW3, SW4	Magnitude Ron SW3—Ron SW4	1		1	Ω
Current Limit	Vswitch (on) = ±10 V	Iswitch	80		220	mA
Isolation	Vswitch (both poles) = ±320 V Logic Inputs = GND	Iswitch	_	_	1	μА
dv/dt Sensitivity*		_	_	200		V/μs

<sup>\*</sup> At 25 °C.

### **Electrical Characteristics** (continued)

Table 4. Ringing Return Switch 3

Parameter	Test Condition	Measure	Min	Тур	Max	Unit
Off-state Leakage Current	Vswitch (differential) = -320 V to Gnd Vswitch (differential) = -60 V to +260 V	Iswitch			1	μΑ
ON Resistance	Iswitch (on) = $\pm 5$ mA, $\pm 10$ mA	Δ Von	_	50*	100	Ω
Current Limit	Vswitch (on) = ±50 V	Iswitch	200	1	400	mA
Isolation	Vswitch = ±320 V Logic Inputs = GND	Iswitch	_	_	1	μА
dv/dt Sensitivity <sup>†</sup>	_			200	_	V/μs

<sup>\*</sup> At 25 °C.

AT&T Microelectronics 4-175

<sup>&</sup>lt;sup>†</sup> Applied voltage is 100 Vpp square wave at 100 Hz.

<sup>&</sup>lt;sup>†</sup> Applied voltage is 100 Vpp square wave at 100 Hz.

### **Electrical Characteristics** (continued)

Table 5. Ringing Switch 4

Parameter	Test Condition	Measure	Min	Тур	Max	Unit
Off-state Leakage Current	Vswitch (differential) = +260 V to -190 V Vswitch (differential) = -260 V to +190 V	Iswitch		_	1	μА
ON Resistance	Iswitch (on) = ±70 mA, ±80 mA	Δ Von	1 —		10	Ω
ON Voltage	Iswitch (on) = ±1 mA	Vos	1 —		3	V
ON Voltage (Vos)	Iswitch (on) = ±1 mA	Vos	l —	-	3	٧
Isolation	Vswitch = ±320 V Logic Inputs = GND	Iswitch	-	—	1	μΑ
Surge Current		_	_	_	2	Α
Release Current	_	_	100	_	500	μА
dv/dt Sensitivity †				200	_	V/μs

<sup>\*</sup> At 25 °C

Table 6. Test Out Switch, 5 and 6

Parameter	Test Condition	Measure	Min	Тур	Max	Unit
Off-state Leakage Current	Vswitch (differential) = -320 V to GND Vswitch (differential) = -60 V to +260 V	Iswitch	-	_	1	μА
ON Resistance	Iswitch (on) = ±5 mA to 10 mA	Δ Von	<b>—</b>	30*	65	Ω
Current Limit	Vswitch (on) = ±50 V	Iswitch	100	_	220	mA
Isolation	Vswitch (both poles) = ±320 V Logic Inputs = GND	Iswitch	_	_	1	μΑ
dv/dt Sensitivity <sup>†</sup>	_		<b>—</b>	200	_	V/µs

<sup>\*</sup> At 25 °C.

**Table 7. Additional Electrical Characteristics** 

Parameter	Test Condition	Measure	Min	Тур	Max	Unit
Digital Input Characteristics:				<u> </u>		
Input Low Voltage	_	_	l —	<u> </u>	1.5	V
Input High Voltage	_	_	3.5		_	٧
Input Leakage Current (High)	$V_{DD} = 5.5 \text{ V}, V_{BAT} = -58 \text{ V},$ $V_{Ogicin} = 5 \text{ V}$	llogicin	_	_	1	μА
Input Leakage Current (Low)	$V_{DD} = 5.5 \text{ V}, V_{BAT} = -58 \text{ V},$ $V_{Ogicin} = 0 \text{ V}$	llogicin	-		1	μА
Power Requirements:						
Power Dissipation	$V_{DD} = 5.5 \text{ V}, V_{BAT} = -58 \text{ V},$ $Idle \text{ or Talk State}$	IDD, IBAT	_	15*	70	mW
VDD Current	VDD = 5.5 V, VBAT = -58 V, Idle or Talk State	loo	_	0.25*	2	mA
VBAT Current	$V_{DD} = 5.5 \text{ V}, V_{BAT} = -58 \text{ V},$ Idle or Talk State	Іват	_	0.25*	1	mA
Temperature Shutdown Requirements: <sup>†</sup>						
Shutdown Activation Temperature	<u> </u>	_	110	125	150	°C
Shutdown Circuit Hysteresis	_	_	10		25	°C

<sup>\*</sup> At 25 °C.

4-176

<sup>&</sup>lt;sup>†</sup> Applied voltage is 100 Vpp square wave at 100 Hz.

 $<sup>^\</sup>dagger$  Applied voltage is 100 Vpp square wave at 100 Hz.

<sup>&</sup>lt;sup>†</sup> Temperature shutdown flag (TSD) will be high during normal operation and low during temperature shutdown state.

### **Zero Cross Current Turn Off**

The ring access switch (SW4) is designed to turn off on a zero current cross. This switch requires a current zero cross at the battery voltage to turn off. Switch 4 (SW4) will remain in the ON state (regardless of logic input) until a current zero cross. Therefore, to ensure proper operation, switch 4 should be connected to the ringing generator (via proper impedance).

#### **SLIC Protection Circuit**

The SLIC protection circuit, shown in Figure 3 as two zener diodes, is included in the ATTL7542 TRAS IC device to protect the battery feed from fault-induced overvoltage situations. With this feature, the only secondary protection required on the line card is the 210 V—250 V protector on the loop side of the solid-state relay. The battery feed is protected by a combination of the current limit in the SLIC break switches (SW3 and SW4) and the SLIC protection circuit.

In reality, this circuit consists of MOSFET transistors that are turned on when the voltage at the battery feed is more negative than the battery or more negative than an internal zener diode reference (clamp voltage). For positive fault conditions, the protection circuit will conduct when the battery feed exceeds one diode drop. The characteristics of the protection circuit are shown in Figures 4 and 5.

Two different clamp voltages are available for the ATTL7542 TRAS IC device. The first alpha character after the numerical device identifier designates the clamp voltage version. The A character designate is intended for a battery voltage of  $-48~V \pm 20\%$  and, the B character designate is intended for battery voltages of  $60~V \pm 20\%$ . Tables 6 and 7 give the specifications for the leakage at the maximum battery voltage (58~V or -72~V), the voltage at which 1 mA is conducted, and the voltage at which the clamp circuit conducts the maximum dc current that can be carried by switches 1 or 2 (ILIMIT SW1, SW2).

The following information shown in Tables 8 and 9 is referenced in Figures 4 and 5.

Compilation of this data was over the full temperature range (-40 °C to +85 °C).

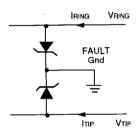


Figure 2. SLIC Protection Circuit

# **SLIC Protection Circuit** (continued)

Table 8. SLIC Protection Circuitry Options (ATTL7542AAE)

				Measure		
Apply	Condition	Figure	Parameter	Min	Max	Unit
RBAT = VBAT TBAT = VBAT	Vbat = -58 V	4	IFAULTGROUND	_	1	μΑ
FAULTGROUND = -1 mA	Vbat = -58 V	4	TBAT RBAT	VBAT + (-4 V)	-	٧
IFAULTGROUND = -ILimit SW1, SW2	Vbat = -58 V	4	Tbat Rbat	VBAT + (-14 V)	_	٧
IFAULTGROUND = +ILIMIT SW1, SW2	Vbat = -58 V	4	TBAT RBAT	_	3	٧
Тват = -60 V (V1 Fig 5) Rват = -60 V (V1 Fig 5)	VBAT = No Connection	5	FAULTGROUND	1	1	μА
FAULTGROUND = -1 mA	VBAT = No Connection	5	Тват (V2 Fig 5) Rват (V2 Fig 5)	-70	_	٧
IFAULTGROUND = + Limit SW1, SW2	VBAT = No Connection	5	<del>_</del>		3	٧

Table 9. SLIC Protection Circuitry Options (ATTL7542BAE)

				Measure	,	
Apply	Condition	Figure	Parameter	Min	Max	Unit
RBAT = VBAT TBAT = VBAT	Vbat = -72 V	4	FAULTGROUND	_	1	μΑ
IFAULTGROUND = −1 mA	VBAT = -72 V	4	T <sub>BAT</sub> RBAT	VBAT + (-4 V)	_	٧
IFAULTGROUND = -ILImit SW1, SW2	VBAT = -72 V	4	TBAT RBAT	VBAT + (-14 V)	_	٧
IFAULTGROUND = +ILimit SW1, SW2	VBAT = −72 V	4	TBAT RBAT		3	٧
Тват = -77 V (V1 Fig 5) Rват = -77 V (V1 Fig 5)	VBAT = No Connection	5	FAULTGROUND	1	1	μА
FAULTGROUND = -1 mA	VBAT = No Connection	5	Тват (V2 Fig 5) Rват (V2 Fig 5)	-87	_	٧
IFAULTGROUND = +ILimit SW1, SW2	VBAT = No Connection	5			3	٧

# **Typical Performance Characteristics**

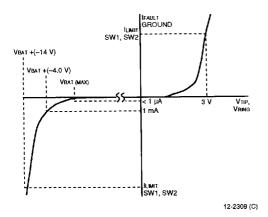


Figure 3. Characteristics of ATTL7542 (VBAT Present)

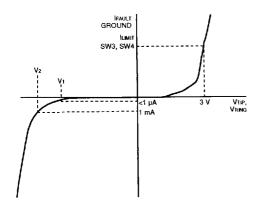


Figure 4. Characteristics of ATTL7542 (VBAT Not Present)

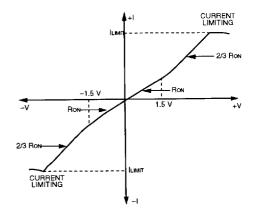


Figure 5. Switch 1-3, 5, 6

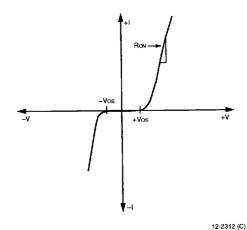


Figure 6. Switch 4

4-179

# **Application**

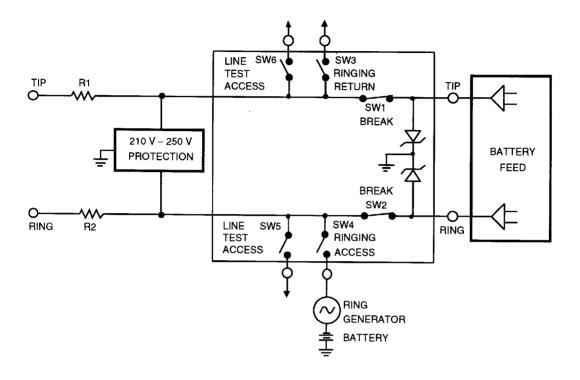


Figure 7. Typical TRAS Application, Idle or Talk State Shown

Table 10. Truth Table

lı	nput		Switches		State Description
Ring	Access	SW 1/2	SW 3/4	SW 5/6	
Low	Low	Closed	Open	Open	Idle or talking state
Low	High	Open	Open	Closed	Line test state
High	Low	Open	Closed	Open	Power ringing state
High	High	Open	Open	Open	All off

# **Application**

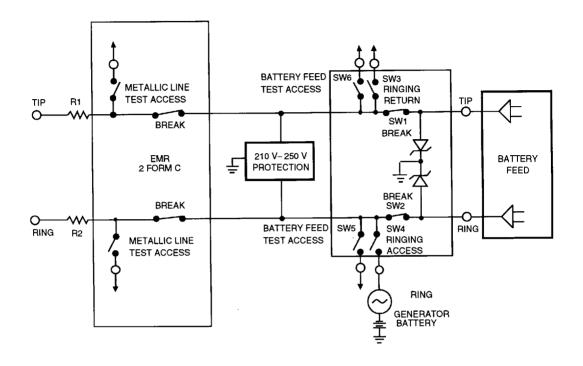


Figure 8. Typical TRAS Application with Metallic Test-in Access, Idle or Talk State Shown

Table 11. Truth Table

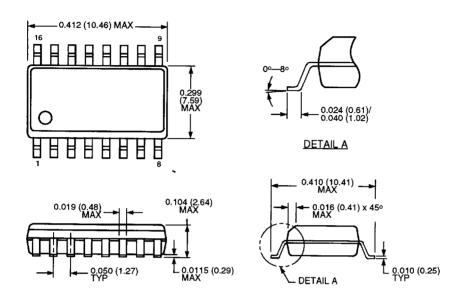
		TRAS				EMR		
li	nput		Switche	s	Input	Swi	itches	State Description
Ring	Access	SW 1/2	SW 3/4	SW 5/6	EMR	EMR Break	EMR Test- in	
Low	Low	Closed	Open	Open	Low	Closed	Open	Idle or talking state
Low	High	Open	Open	Closed	Low	Closed	Open	Line test state
Low	Low	Closed	Open	Open	High	Open	Closed	Battery feed test state
High	Low	Open	Closed	Open	Low	Closed	Open	Power ringing state
High	Low	Open	Closed	Open	High	Open	Closed	Ringing generator test state*
High	High	Open	Open	Open	Low	Closed	Open	All off

<sup>\*</sup> Power ringing appears at test node.

# **Outline Drawings**

Dimensions are in inches and (millimeters).

### 16-Pin, Plastic SOG



# **Packaging and Ordering Information**

Throughout this section the following abbreviations are used:

DIP — Dual in-line package; SOG — Small-outline gull wing; SOJ — Small-outline J-lead; SONB — Small-outline narrow body; PLCC — Plastic leaded chip carrier.

Device Code	Package Type	Temperature
ATTL7551AP	44-Pin PLCC	-40 °C to +85 °C
ATTL7551AF	24-Pin DIP	–40 °C to +85 °C
ATTL7554AP	44-Pin PLCC	–40 °C to +85 °C
ATTL7556AAU	32-Pin PLCC	-40 °C to +85 °C
ATTL7557AAU	32-11111200	
ATTL7561AP	44-Pin PLCC	–40 °C to +85 °C
ATTL7564AP	44-1111 200	
ATTL7581AC/BC	16-Pin DIP	-40 °C to +85 °C
ATTL7581AAE/BAE	16-Pin Plastic SOG	-40 °C to +85 °C
ATTL7582AE/BE	16-Pin Plastic DIP	-40 °C to +85 °C
ATTL7582AAE/BAE	16-Pin Plastic SOG	-40 °C to +85 °C
ATTL7583AF/BF	24-Pin Plastic DIP (600 mil)	–40 °C to +85 °C
ATTL7583ACG/BCG	24-Pin Plastic DIP (300 mil)	-40 °C to +85 °C
ATTL7583AAJ/BAJ	28-Pin Plastic SOG	-40 °C to +85 °C
ATTL7590AAF	14-Pin	-40 °C to +85 °C
ATTL7591AB	8-Pin, DIP	-40 °C to +85 °C
ATTL7591AS	8-Pin, SONB	-40 °C to +85 °C
LB1011AB	8-Pin, DIP	–20 °C to +70 °C
LB1013AD	18-Pin, DIP	-25 °C to +85 °C
LB1060AB	8-Pin, DIP	-40 °C to +65 °C
LB1201AB	8-Pin, DIP	-40 °C to +85 °C
LB1201AS	8-Pin, SONB	–40 °C to +85 °C
LB1208AAJ	28-pin SOG	-40 °C to +85 °C
LB1276AP	44-Pin PLCC	-40 °C to +85 °C
LB1276AF	24-Pin DIP	–40 °C to +85 °C
LB1356AF	24-Pin DIP	-40 °C to +85 °C
LH1263AR	20-Pin Plastic DIP	-40 °C to +85 °C
LH1571AB	8-pin Plastic DIP	-40 °C to +85 °C
LH1571AAC	8-pin SOG	-40 °C to +85 °C
T - 7503 EL	20-Pin, SOJ	-40 °C to +85 °C
T - 7503 1EC	20-Pin, SOJ	0 °C to 70 °C
T - 7504 PL	28-Pin, DIP	-40 °C to +85 °C
T - 7504 ML	28-Pin, PLCC	-40 °C to +85 °C
T - 5504 PL	28-Pin, DIP	-40 °C to +85 °C
T - 5504 ML	28-Pin, PLCC	-40 °C to +85 °C
T - 7513B EE	20-Pin, SOJ	-40 °C to +85 °C
T - 7513B PE	20-Pin, DIP	-40 °C to +85 °C
T - 7517A EE	16-Pin, DIP	-40 °C to +85 °C
T - 7517A PE	16-Pin, SOJ	–40 °C to +85 °C
T - 7548 ME2	28-Pin, PLCC	0 °C to 85 °C
T - 7570 ML2	28-Pin, PLCC	-40 °C to +85 °C